

IN THE CLAIMS

Applicant respectfully requests that the claims of the above-identified application be amended so as to read as follows thereby to place the claims of the above-identified application in condition for allowance. or at least in better form for Appeal, pursuant to 37 CFR 1.116:

1. (Previously Presented) A plasma processing apparatus generating plasma under atmospheric pressure for processing an object, comprising:
 - first and second electrodes adjacent to each other and having coated surfaces facing a surface of the object to be processed;
 - a dielectric having a first opposing surface positioned spaced apart from the surface of the object between the object and said first electrode and a second opposing surface positioned spaced apart from the surface of the object between the object and said second electrode, completely filled between said first and second electrodes and covering said coated surfaces;
 - gas supplying means provided through the inside of only the first electrode of said first and second electrodes, and having a supply opening formed in said first opposing surface for supplying a processing gas to the surface of the object through said supply opening; and
 - gas exhausting means provided through the inside of only the second electrode of said first and second electrodes, and having an exhaust opening formed in said second opposing surface for exhausting the processing gas supplied to the surface of the object through said exhaust opening.
2. (Canceled, without prejudice)

3. (Previously Presented) The plasma processing apparatus according to claim 1, wherein around said gas supplying means and said gas exhausting means, an inner wall formed of a dielectric material is provided.
4. (Original) The plasma processing apparatus according to claim 1, wherein the coated surfaces of said first and second electrodes, respectively, extend on a plane parallel to the surface of the object.
5. (Original) The plasma processing apparatus according to claim 1, wherein an electric line of force connecting said first and second electrodes when a voltage is applied between said first and second electrodes extends above and substantially parallel to the surface of the object.
6. (Original) The plasma processing apparatus according to claim 1, wherein said supply opening and said exhaust opening are provided in a vicinity of a region positioned between said first opposing surface and said second opposing surface.
7. (Currently Amended) A The plasma processing apparatus according to claim 1, wherein
~~generating plasma under atmospheric pressure for processing an object,~~
~~comprising:~~
~~first and second electrodes adjacent to each other and having coated surfaces facing a~~
~~surface of the object to be processed;~~
~~a dielectric having a first opposing surface positioned spaced apart from the surface of the~~
~~object between the object and said first electrode and a second opposing surface~~
~~positioned spaced apart from the surface of the object between the object and~~
~~said second electrode;~~

~~said dielectric completely filled between said first and second electrodes and covering
said coated surfaces;~~

said dielectric ~~including~~ includes a recessed portion formed such that the distance from
the surface of the object to said second opposing surface is made larger than the
distance from the surface of the object to said first opposing surface; and

~~gas supplying means provided inside said first electrode having a supply opening formed
in said first opposing surface for supplying a processing gas to the surface of the
object through said supply opening; and~~

~~gas exhausting means provided inside said second electrode having an exhaust opening
formed in said second opposing surface for exhausting the processing gas
supplied to the surface of the object through said exhaust opening;~~

wherein said the exhaust opening being is located at the recessed portion of the second
opposing surface.

8. (Original) The plasma processing apparatus according to claim 1, wherein said supply opening
and said exhaust opening are formed to have a slit-shape extending in one
direction or formed as a plurality of pores arranged in one direction.

9. (Original) The plasma processing apparatus according to claim 1, wherein said gas supplying
means and said gas exhausting means are formed such that total flow rate of gas
exhausted through said exhaust opening is not smaller than total flow rate of the
processing gas supplied through said supply opening.

10. (Original) The plasma processing apparatus according to claim 1, wherein at that portion of said dielectric which faces the surface of the object, where distance between an end portion of said dielectric positioned at a shortest distance from said supply opening and said supply opening is represented by $L1$, distance between said supply opening and said exhaust opening is represented by $L2$, and distance between said exhaust opening and an end portion of said dielectric positioned at a shortest distance from said exhaust opening is represented by $L3$, $L1$, $L2$ and $L3$ satisfy the relations of $4 \leq L1/L2 \leq 1000$ and $4 \leq L3/L2 \leq 1000$.
11. (Original) The plasma processing apparatus according to claim 1, further comprising a grounded conductive cover provided to cover externally exposed surfaces of said first and second electrodes.
12. (Original) The plasma processing apparatus according to claim 1, further comprising a third electrode positioned next to said second electrode on a side opposite to said first electrode with respect to said second electrode, said apparatus being formed in symmetry with respect to said second electrode.